

## Depletion-Mode Power MOSFET

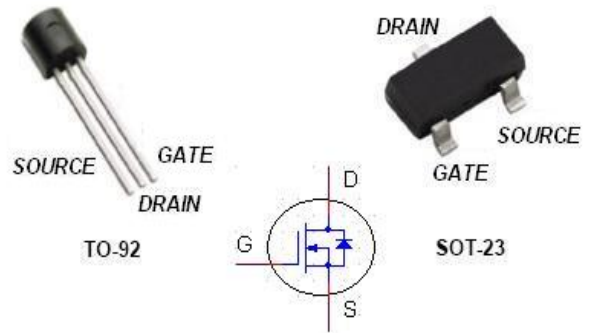
### General Features

- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Low  $R_{DS(ON)}$  Minimizes Conduction Loss
- Fast Switching Speed
- RoHS Compliant/Lead Free

$BV_{DSX}$	$R_{DS(ON)}$ (Max.)	$I_{DSS,min}$
550V	60 $\Omega$	200mA

### Applications

- Normally-on Switches
- Solid State Relay
- Linear Amplifier
- Converters
- Constant Current Source
- Power Supply Circuit
- Telecom



### Ordering Information

Part Number	Package	Marking
DMN5501	TO-92	DMN5501
DMZ5501	SOT-23	5501

### Absolute Maximum Ratings

$T_A=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	DMN5501	DMZ5501	Unit
$V_{DSX}$	Drain-to-Source Voltage <sup>[1]</sup>	550		V
$V_{DGX}$	Drain-to-Gate Voltage <sup>[1]</sup>	550		V
$I_D$	Continuous Drain Current	72 <sup>[1]</sup>	59 <sup>[1]</sup>	mA
$I_{DM}$	Pulsed Drain Current	290	240	
$P_D$	Power Dissipation	0.74	0.50	W
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$		V
$T_L$	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300		$^{\circ}\text{C}$
$T_J$ and $T_{STG}$	Operating and Storage Temperature Range	-55 to 150		

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

### Thermal Characteristics

Symbol	Parameter	DMN5501	DMZ5501	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	170	250	K/W

## Electrical Characteristics

### OFF Characteristics

 $T_A = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$BV_{DSX}$	Drain-to-Source Breakdown Voltage	550	--	--	V	$V_{GS} = -10\text{V}$ , $I_D = 100\mu\text{A}$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	10	$\mu\text{A}$	$V_{DS} = 550\text{V}$ , $V_{GS} = -10\text{V}$
		--	--	1.0	mA	$V_{DS} = 440\text{V}$ , $V_{GS} = -10\text{V}$ $T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Leakage Current	--	--	100	nA	$V_{GS} = +20\text{V}$ , $V_{DS} = 0\text{V}$
		--	--	-100		$V_{GS} = -20\text{V}$ , $V_{DS} = 0\text{V}$

### ON Characteristics

 $T_A = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$I_{DSS}$	Saturated Drain-to-Source Current	200	--	--	mA	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	50	60	$\Omega$	$V_{GS} = 0\text{V}$ , $I_D = 10\text{mA}$ <sup>[4]</sup>
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature	--	--	1.0	%/ $^\circ\text{C}$	$V_{GS} = 0\text{V}$ , $I_D = 10\text{mA}$
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-4.0	--	-2.0	V	$V_{DS} = 25\text{V}$ , $I_D = 10\mu\text{A}$
$\Delta V_{GS(OFF)}$	Change in $V_{GS(OFF)}$ with Temperature	--	--	-6.0	mV/ $^\circ\text{C}$	$V_{DS} = 25\text{V}$ , $I_D = 10\mu\text{A}$
gfs	Forward Transconductance	100	150	--	mS	$V_{DS} = 10\text{V}$ , $I_D = 100\text{mA}$

### Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$C_{ISS}$	Input Capacitance	--	--	450	pF	$V_{GS} = -10\text{V}$ $V_{DS} = 25\text{V}$ $f = 1.0\text{MHz}$
$C_{OSS}$	Oput Capacitance	--	--	20		
$C_{RSS}$	Reverse Transfer Capacitance	--	--	13		
$Q_G$	Total Gate Charge	--	0.33	0.40	nC	$V_{GS} = -5\text{V} \sim 5\text{V}$ $V_{DS} = 275\text{V}$ , $I_D = 10\text{mA}$
$Q_{GS}$	Gate-to-Source Charge	--	1.8	2.0		
$Q_{GD}$	Gate-to-Drain (Miller) Charge	--	3.0	3.4		

### Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	--	--	ns	$V_{GS} = -10\text{V} / 0\text{V}$ $V_{DD} = 275\text{V}$ , $I_D = 10\text{mA}$ $R_G = 250\Omega$
$t_{rise}$	Rise Time	--	--	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	--	--		
$t_{fall}$	Fall Time	--	--	--		

**Source-Drain Diode Characteristics** $T_A=25^{\circ}\text{C}$  unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
$V_{SD}$	Diode Forward Voltage	--	--	1.2	V	$I_{SD} = 10 \text{ mA}$ , $V_{GS} = -10 \text{ V}$
$t_{rr}$	Reverse Recovery Time	--	5.0	6.0	ns	$V_R=275\text{V}$ $I_F=10\text{mA}$ , $dI_F/dt=100\text{A/us}$
$Q_{rr}$	Reverse Recovery Charge	--	48	55	nC	

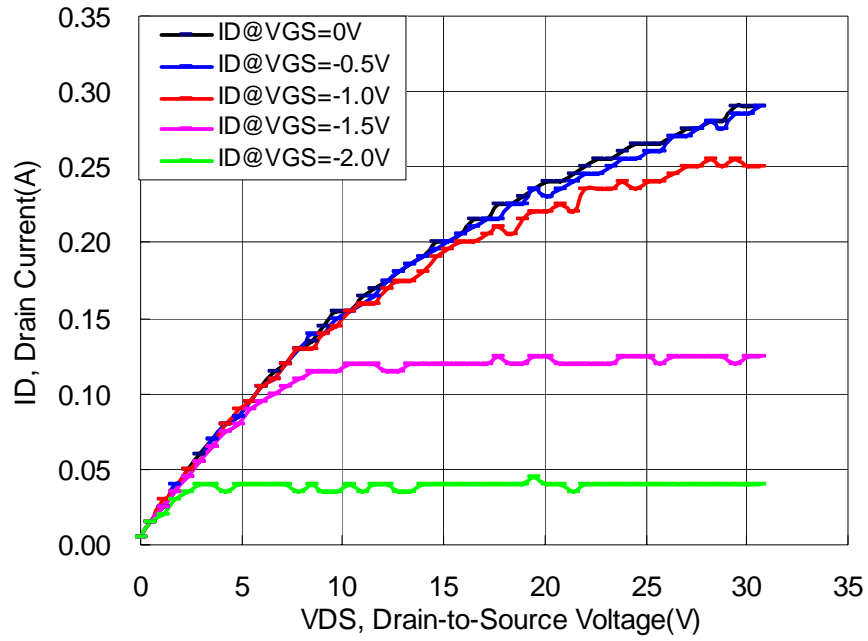
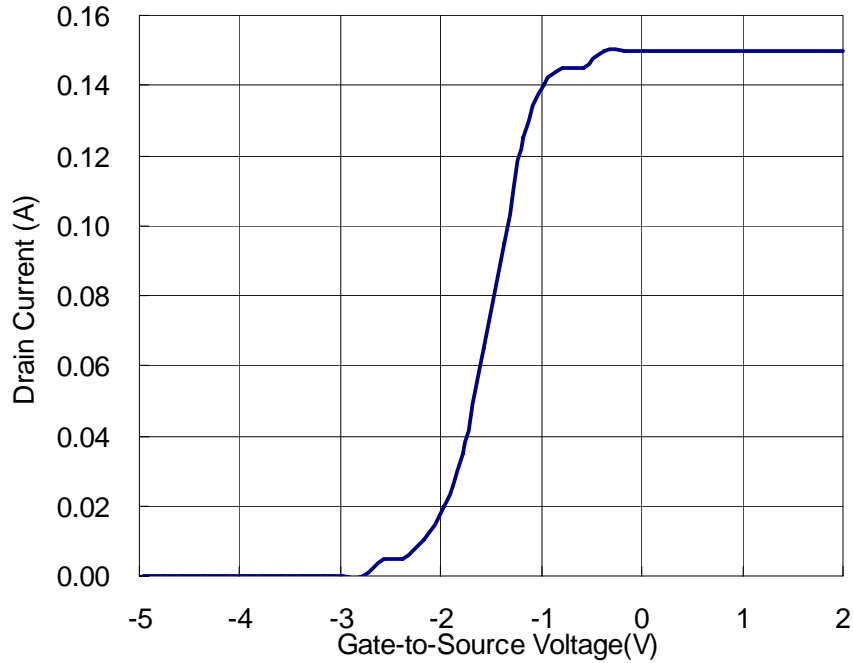
**NOTE:**

[1]  $I_D$  is limited by the maximum junction temperature.

[2]  $T_J=+25^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

[3] Repetitive rating, pulse width limited by maximum junction temperature.

[4] Pulse width  $\leq 380\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**Typical Performance Curves**
**Output Characteristics**

**Transfer Characteristics**




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